

## NCE N-Channel Enhancement Mode Power MOSFET

### Description

The NCE40H11 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

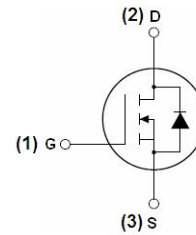
- $V_{DS} = 40V, I_D = 110A$   
 $R_{DS(ON)} < 4.0m\Omega @ V_{GS} = 10V$   
 $R_{DS(ON)} < 6.5m\Omega @ V_{GS} = 4.5V$
- High density cell design for ultra low  $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation

### Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

**100% UIS TESTED!**

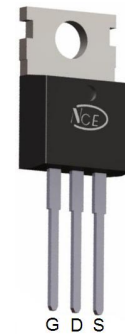
**100%  $\Delta V_{DS}$  TESTED!**



Schematic diagram



Marking and pin assignment



TO-220-3L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40H11	NCE40H11	TO-220-3L	-	-	-

### Absolute Maximum Ratings ( $T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	110	A
Drain Current-Continuous( $T_c = 100^\circ C$ )	$I_D(100^\circ C)$	77.8	A
Pulsed Drain Current	$I_{DM}$	440	A
Maximum Power Dissipation	$P_D$	105	W
Derating factor		0.7	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	$E_{AS}$	540	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	1.43	°C/W
Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	55	°C/W

## Electrical Characteristics ( $T_c=25^{\circ}\text{C}$ unless otherwise noted)

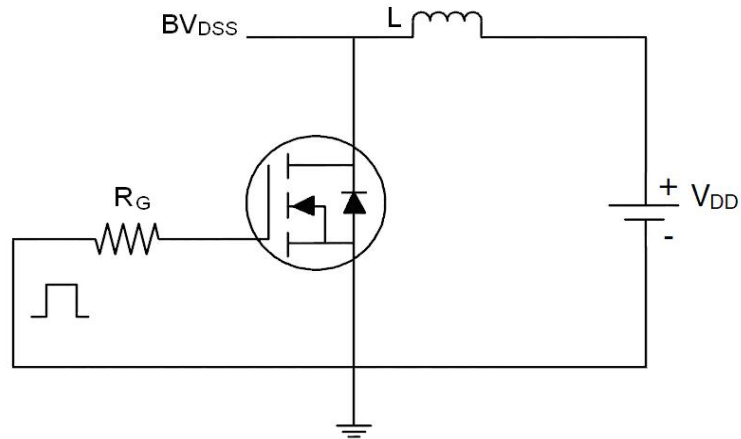
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	40	45	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics <small>(Note 3)</small>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.2	1.6	2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	3.4	4.0	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	-	5.1	6.5	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =20A	26	-	-	S
Dynamic Characteristics <small>(Note4)</small>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, F=1.0MHz	-	3650	-	PF
Output Capacitance	C <sub>oss</sub>		-	382	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	340	-	PF
Switching Characteristics <small>(Note 4)</small>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =20V, R <sub>L</sub> =1Ω V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω	-	14	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	17	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	50	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	22	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =20V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V	-	84		nC
Gate-Source Charge	Q <sub>gs</sub>		-	10		nC
Gate-Drain Charge	Q <sub>gd</sub>		-	22		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <small>(Note 3)</small>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	-	1.2	V
Diode Forward Current <small>(Note 2)</small>	I <sub>S</sub>		-	-	110	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = 20A di/dt = 100A/μs <sup>(Note3)</sup>	-	42	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	45	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

## Notes:

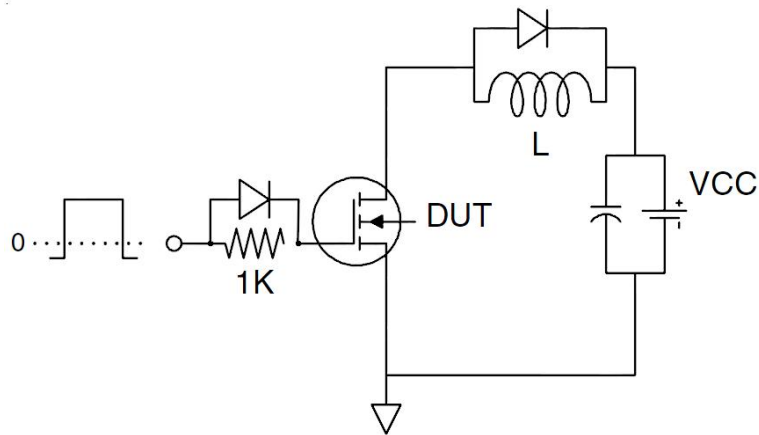
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec. The value of  $R_{\theta JA}$  is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^{\circ}\text{C}$ . The Power dissipation PDSM is based on  $R_{\theta JA}$  and the maximum allowed junction temperature of  $150^{\circ}\text{C}$ . The value in any given application depends on the user's specific board design, and the maximum temperature of  $175^{\circ}\text{C}$  may be used if the PCB allows it.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5.  $E_{AS}$  condition :  $T_J=25^{\circ}\text{C}, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega$ .

## Test circuit

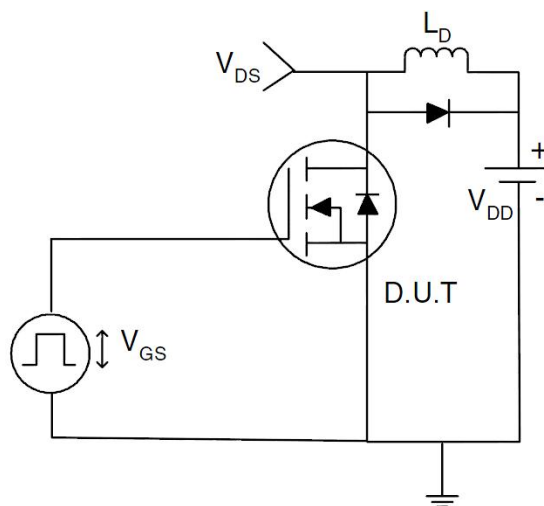
### 1) $E_{AS}$ Test Circuit



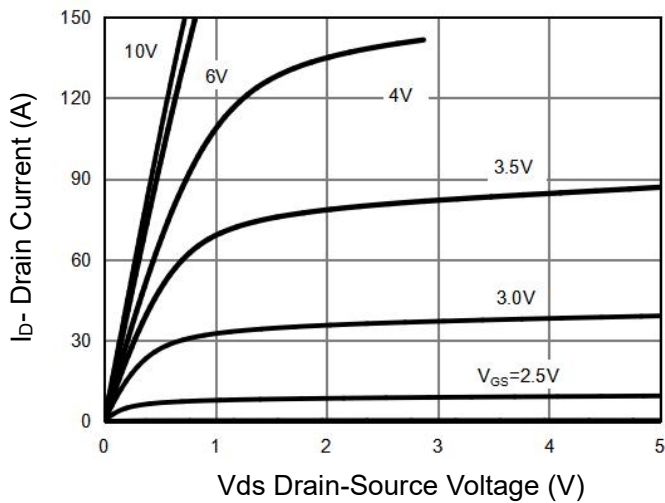
### 2) Gate Charge Test Circuit



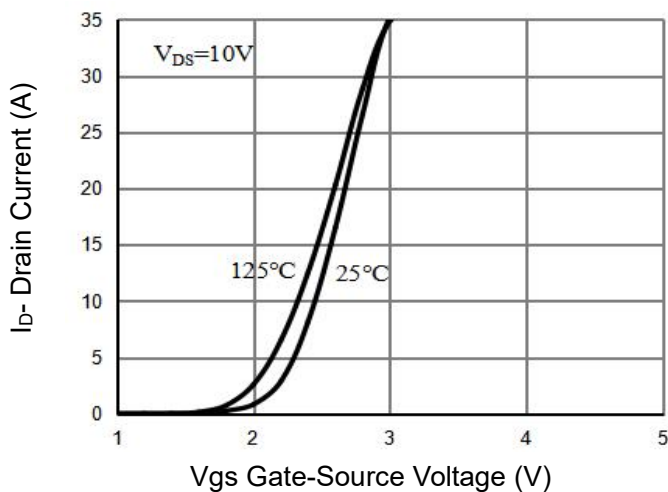
### 3) Switch Time Test Circuit



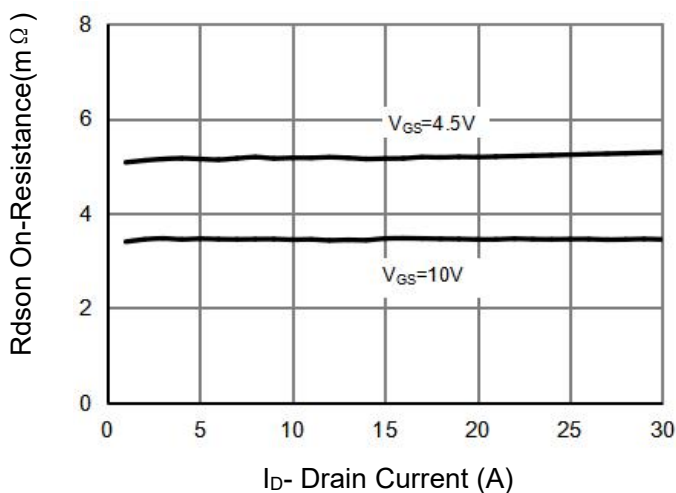
## Typical Electrical and Thermal Characteristics (Curves)



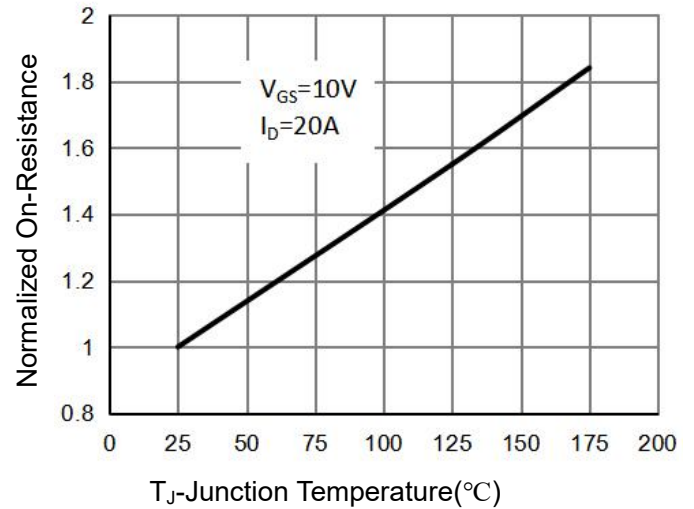
**Figure 1 Output Characteristics**



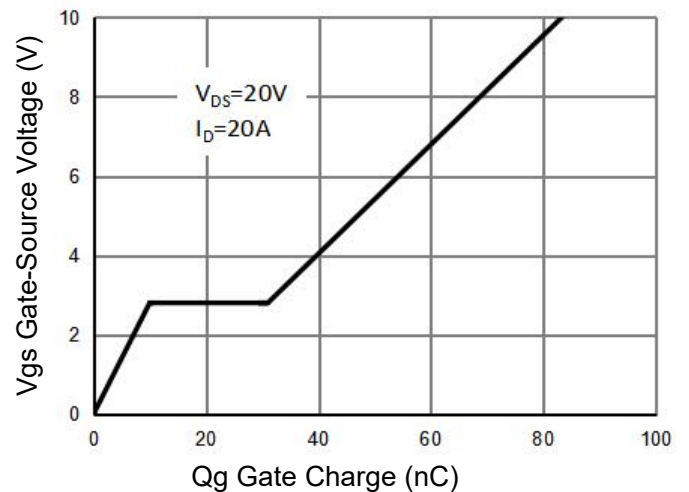
**Figure 2 Transfer Characteristics**



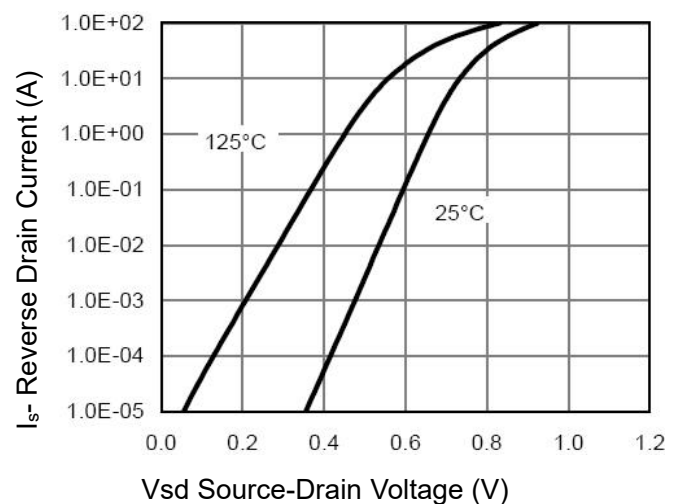
**Figure 3 Rdson- Drain Current**



**Figure 4 Rdson-Junction Temperature**



**Figure 5 Gate Charge**



**Figure 6 Source- Drain Diode Forward**

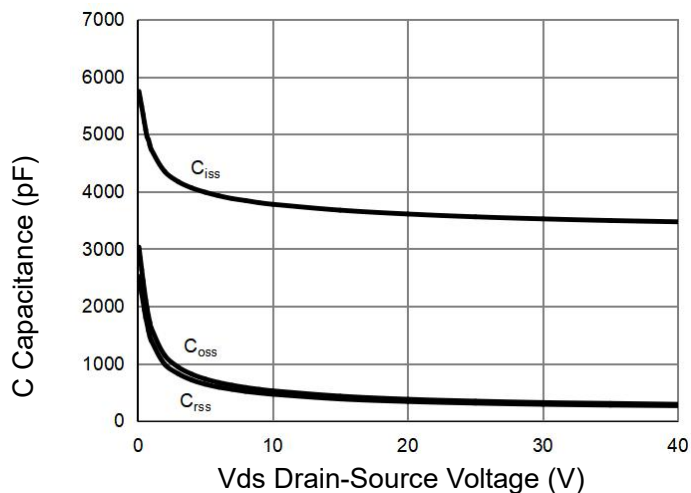


Figure 7 Capacitance vs Vds

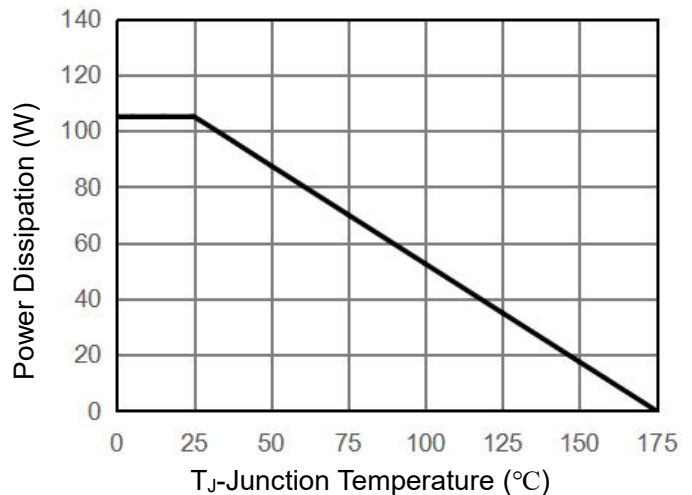


Figure 9 Power De-rating

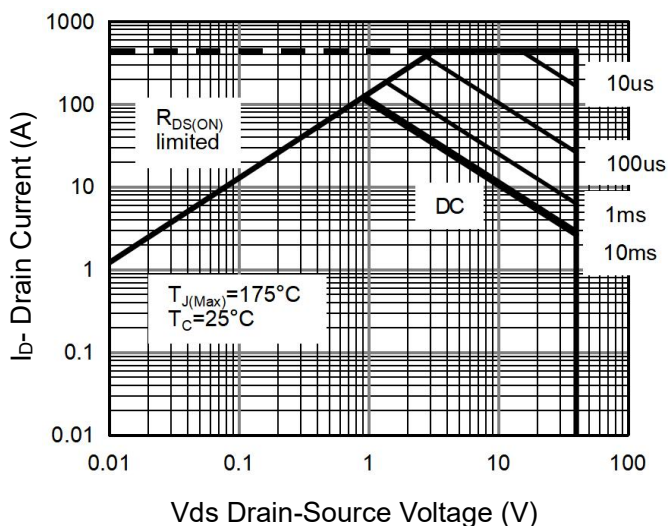


Figure 8 Safe Operation Area

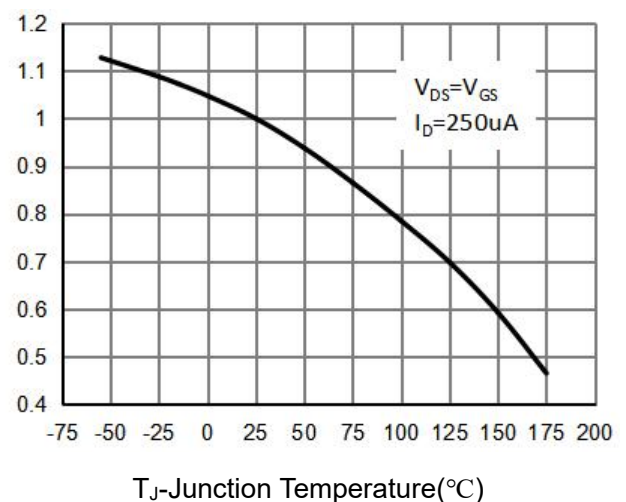
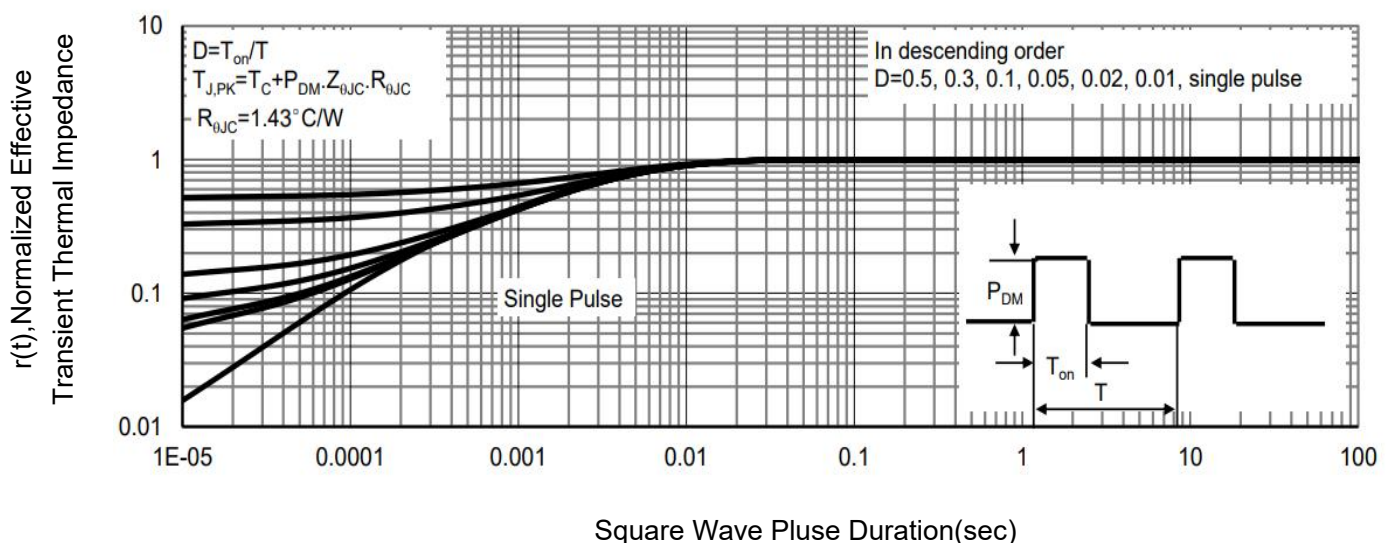
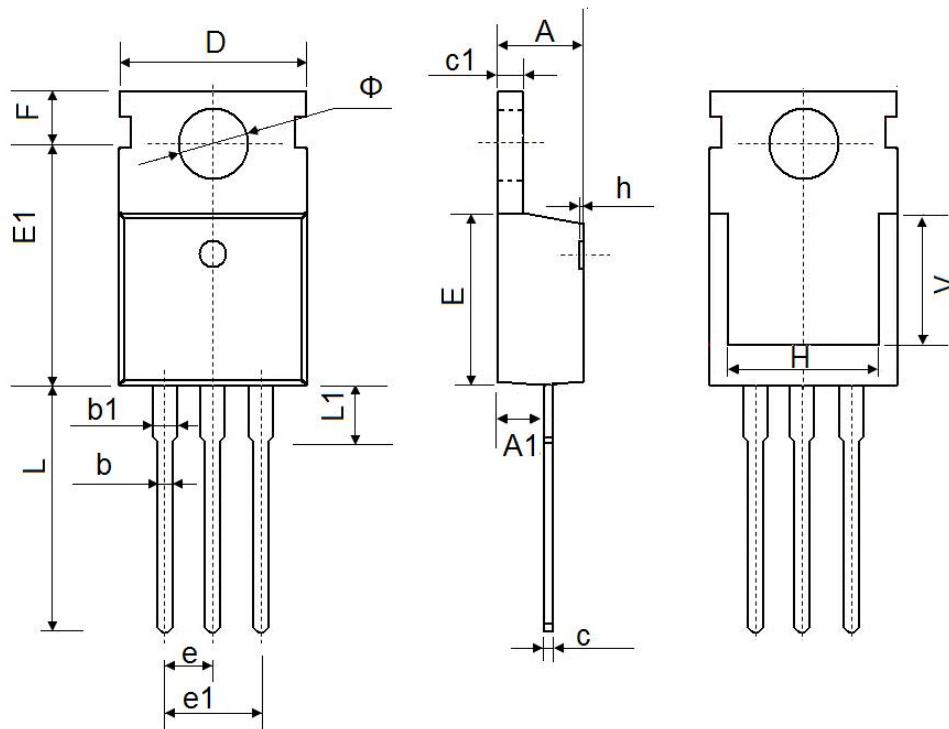

Figure 10  $V_{GS(th)}$  vs Junction Temperature


Figure 11 Normalized Maximum Transient Thermal Impedance

## TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

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